

SANYO

No.1047B

2SA1246/2SC3114

PNP/NPN Epitaxial Planar Silicon Transistors

High- V_{EBO} , AF Amp Applications**Features**

- High V_{EBO}
- Wide ASO and highly resistant to breakdown.

(): 2SA1246

Absolute Maximum Ratings/ $T_a = 25^\circ\text{C}$

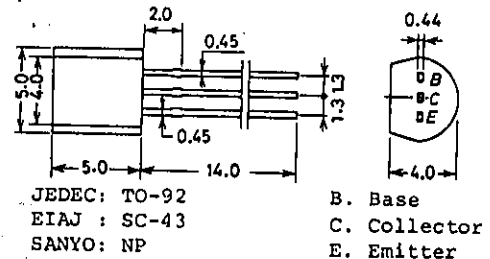
			unit
Collector to base voltage	V_{CBO}	(-)60	V
Collector to emitter voltage	V_{CEO}	(-)50	V
Emitter to base voltage	V_{EBO}	(-)15	V
Collector current	I_C	(-)150	mA
Collector Current(Pulse)	I_{CP}	(-)300	mA
Collector dissipation	P_C	400	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics/ $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Collector cutoff current	I_{CBO}	$V_{CB}=(-)40\text{ V}, I_E=0$			(-)0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=(-)10\text{ V}, I_C=0$			(-)0.1	μA
DC current gain	h_{FE}	$V_{CE}=(-)6\text{ V}, I_C=(-)1\text{ mA}$	100*		560*	
Gain-bandwidth product	f_T	$V_{CE}=(-)6\text{ V}, I_C=(-)1\text{ mA}$		100		MHz
Common base output capacitance	C_{ob}	$V_{CB}=(-)6\text{ V}, f=1\text{ MHz}$		3.0		pF
C-E saturation voltage	$V_{CE(sat)}$	$I_C=(-)50\text{ mA}, I_B=(-)5\text{ mA}$		(4.2)	(-)0.5	V
C-B breakdown voltage	$V_{(BR)CBO}$	$I_C=(-)10\text{ }\mu\text{A}, I_E=0$	(-)60			V
C-E breakdown voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{ mA}, R_{BE}=\infty$	(-)50			V
E-B breakdown voltage	$V_{(BR)EBO}$	$I_E=(-)10\text{ }\mu\text{A}, I_C=0$	(-)15			V

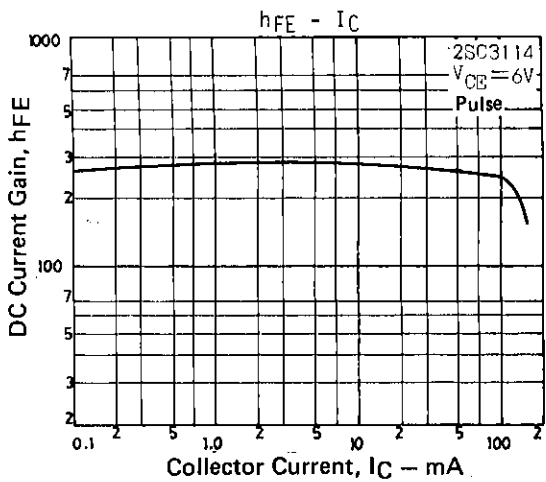
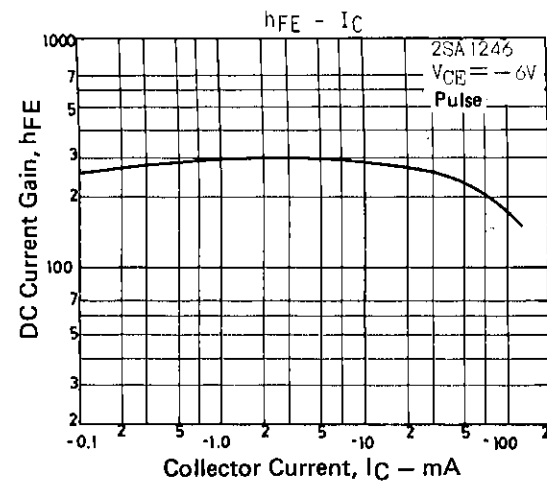
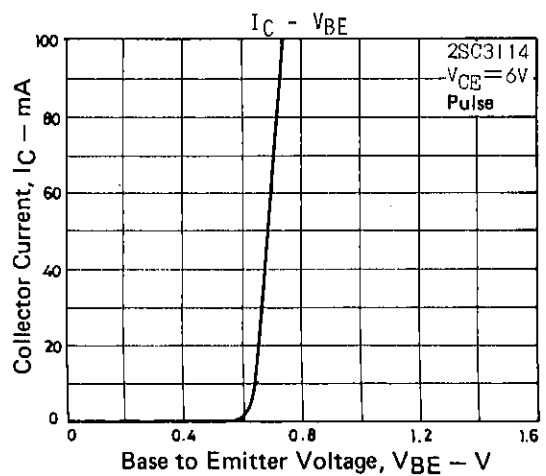
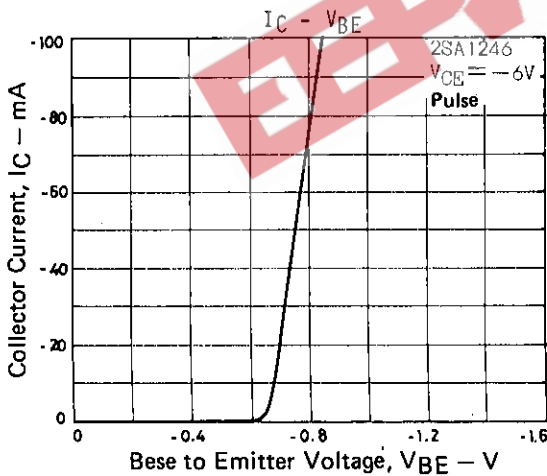
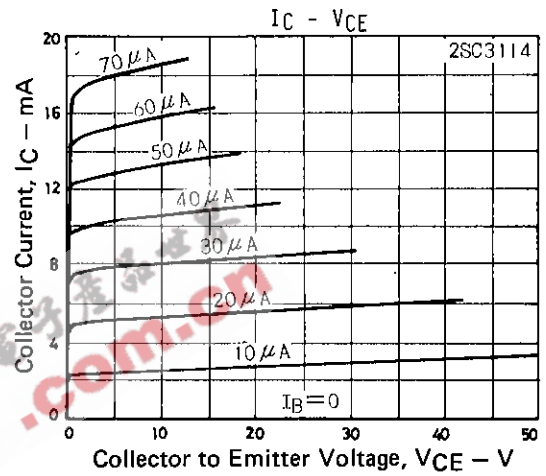
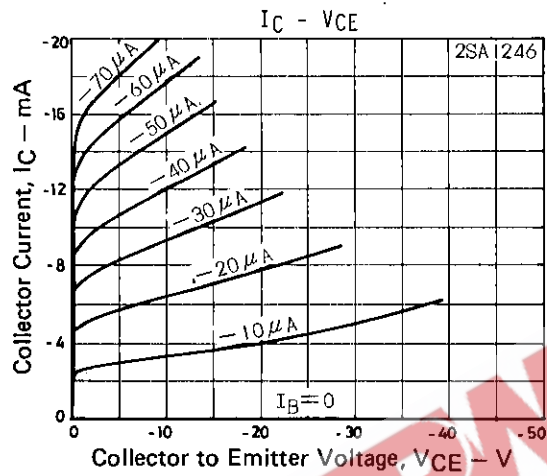
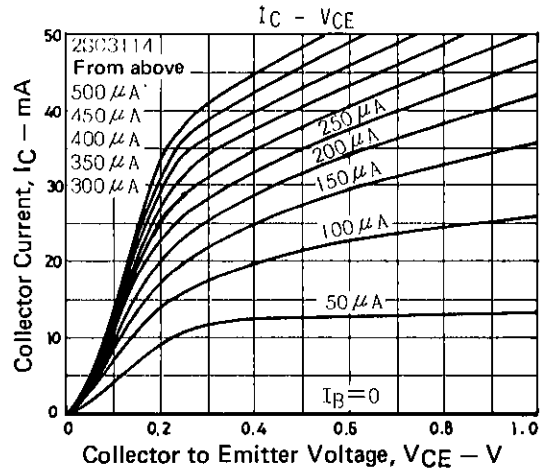
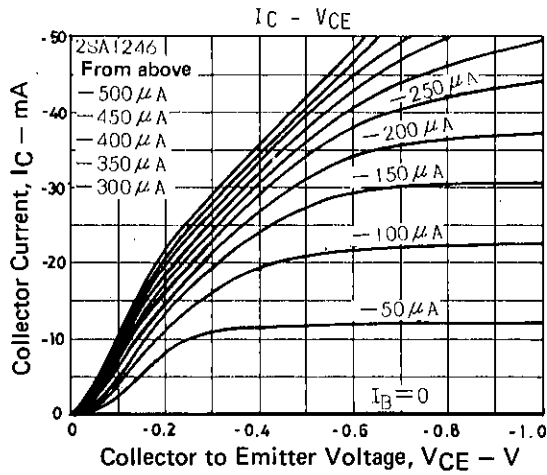
* The 2SA1246/2SC3114 are classified as follows according to h_{FE} at 1 mA.

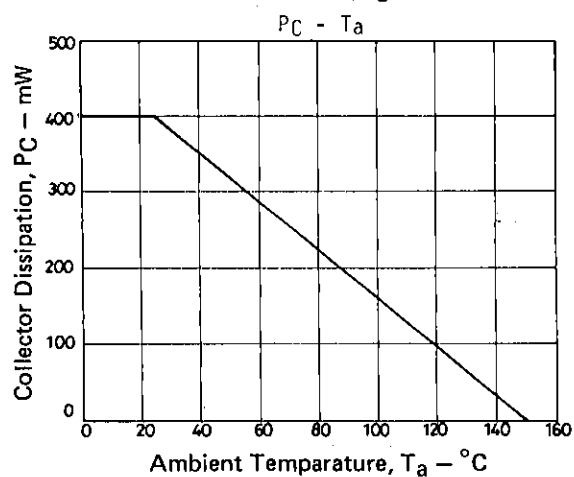
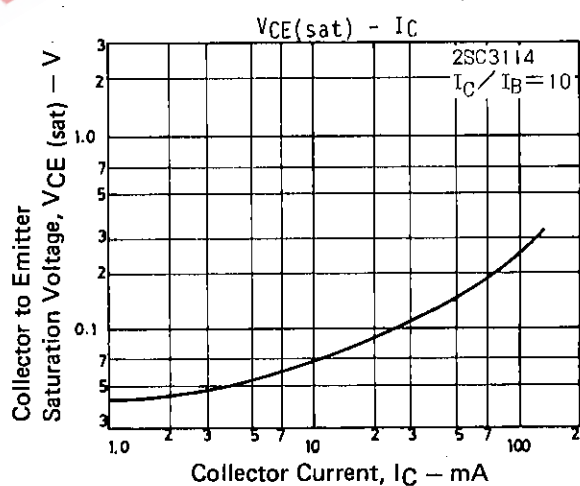
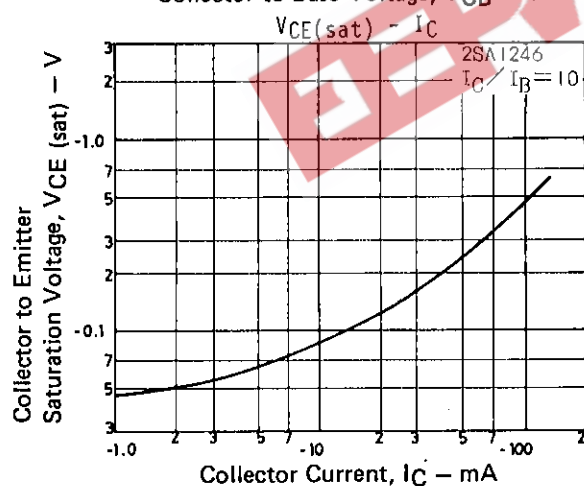
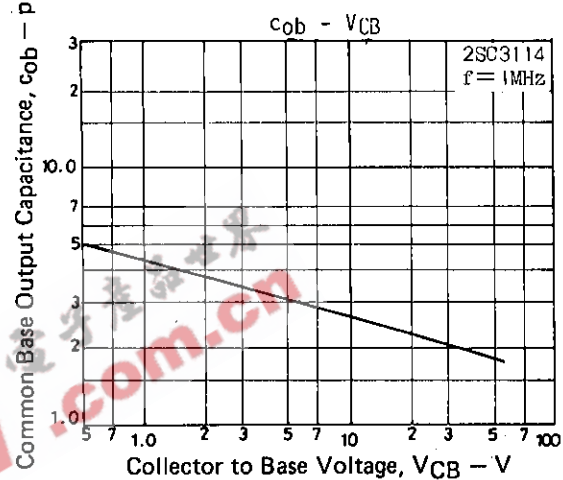
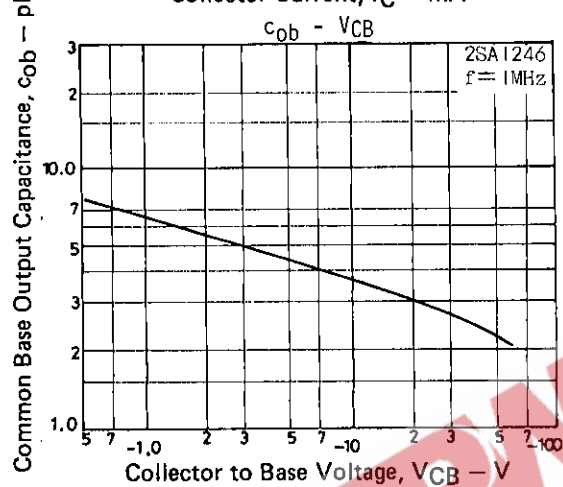
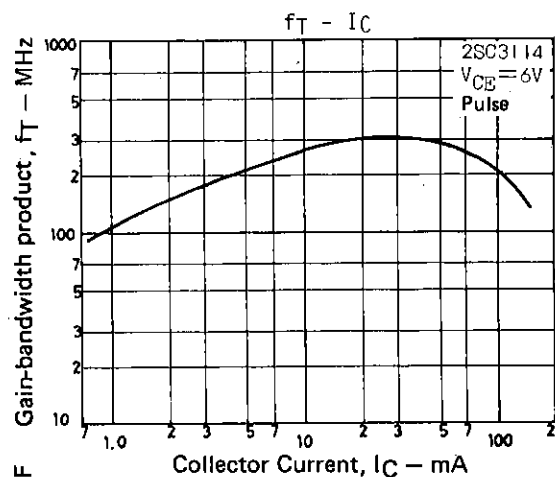
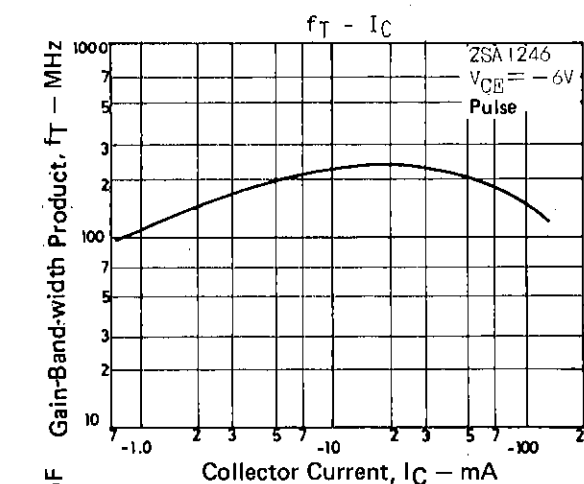
100 R 200	140 S 280	200 T 400	280 U 560
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Package Dimensions 2003A
(unit: mm)**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**

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